

Description

The SXG120N12NF uses advanced **SGT II** technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 120V$ $I_D = 120A$

$R_{DS(ON)} < 6.8m\Omega$ @ $V_{GS} = 10V$

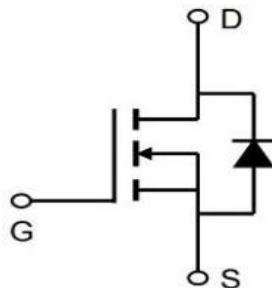
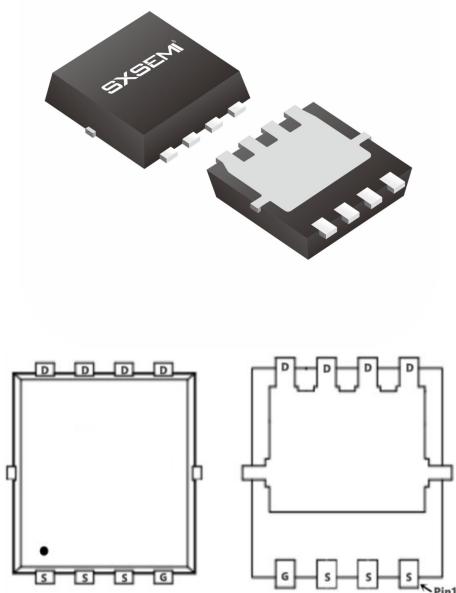
Application

Mobile phone fast charging

Brushless motor

Home appliance control board

PDFN5*6-8L



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
$VDSS$	Drain-to-Source Voltage	120	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current ¹	120	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current ¹	70	A
IDM^{a1}	Pulsed Drain Current	320	A
$EASa2$	Single pulse avalanche energy	240	mJ
IAR	Single pulse avalanche current	40	A
VGS	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	125	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
T_L	Maximum Temperature for Soldering	300	°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
VDSS	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	120	135	--	V
IDSS	Drain to Source Leakage Current	$V_{DS} = 120\text{V}, V_{GS}= 0\text{V}$	--	--	1	μA
IGSS(F)	Gate to Source Forward Leakage	$V_{GS} =+20\text{V}$	--	--	100	nA
IGSS(R)	Gate to Source Reverse Leakage	$V_{GS} =-20\text{V}$	--	--	-100	nA
VGS(TH)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D = 250\mu\text{A}$	1.2	1.8	3.0	V
RDS(ON)1	Drain-to-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$	--	6.0	6.8	$\text{m}\Omega$
RDS(ON)1	Drain-to-Source On-Resistance	$V_{GS}=4.5\text{V}, I_D=10\text{A}$	--	8.5	10	$\text{m}\Omega$
gFS	Forward Transconductance	$V_{DS}=5\text{V}, I_D=50\text{A}$		130	--	S
Ciss	Input Capacitance	$V_{GS} = 0\text{V} \quad V_{DS} = 50\text{V} \quad f = 1.0\text{MHz}$	--	4282	--	pF
Coss	Output Capacitance		--	429	--	pF
Crss	Reverse Transfer Capacitance		--	17	--	pF
R _g	Gate resistance		--	2.5	--	Ω
td(ON)	Turn-on Delay Time	$I_D = 20\text{A}$ $V_{DS} = 50\text{V}$ $V_{GS} = 10\text{V}$ $R_G = 5\Omega$	--	20	--	ns
tr	Rise Time		--	11	--	ns
td(OFF)	Turn-Off Delay Time		--	55	--	ns
tf	Fall Time		--	28	--	ns
Q _g	Total Gate Charge	$V_{GS} = 0\sim 10\text{V}$ $V_{DS} = 50\text{V}$ $I_D = 20\text{A}$	--	61.4	--	nC
Qgs	Gate Source Charge		--	17.4	--	nC
Qgd	Gate Drain Charge		--	14.1	--	nC
IS	Diode Forward Current	$T_C = 25^\circ\text{C}$	--	--	100	A
ISM	Diode Pulse Current		--	--	320	A
VSD	Diode Forward Voltage	$I_S=6.0\text{A}, V_{GS}=0\text{V}$	--	--	1.2	V
trr	Reverse Recovery time	$I_S=20\text{A}, V_{DD}=50\text{V}$ $dI/dt=100\text{A}/\mu\text{s}$	--	100	--	ns
Qrr	Reverse Recovery Charge		--	250	--	nC

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $VDD=50\text{V}$, $L=0.3\text{mH}$, $R_g=25\Omega$, Starting $TJ=25^\circ\text{C}$
- 4、The power dissipation is limited by 150°C junction temperature

Typical Characteristics

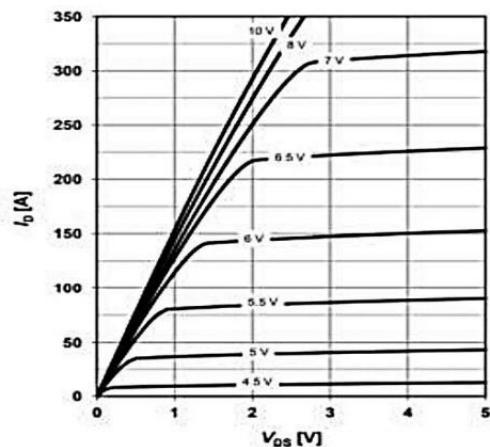


Figure1: output characteristics

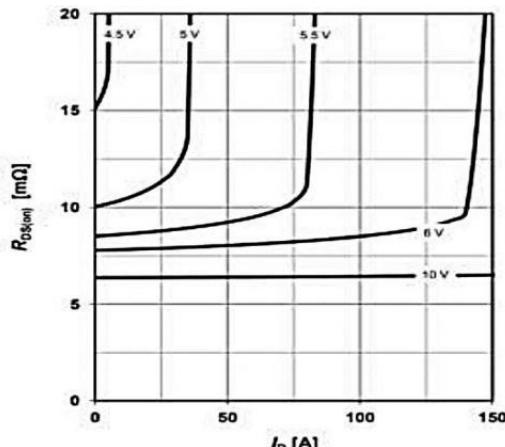


Figure2: Typcal drain-source on resistance

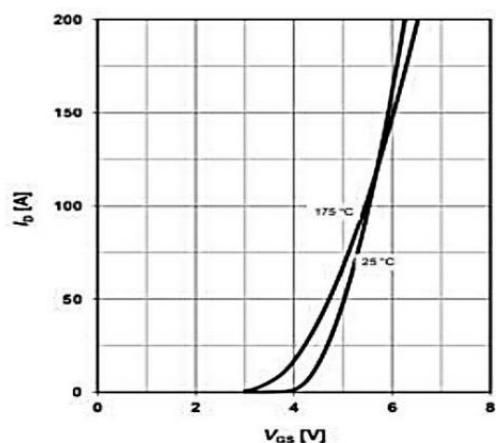


Figure3: transfer characteristics

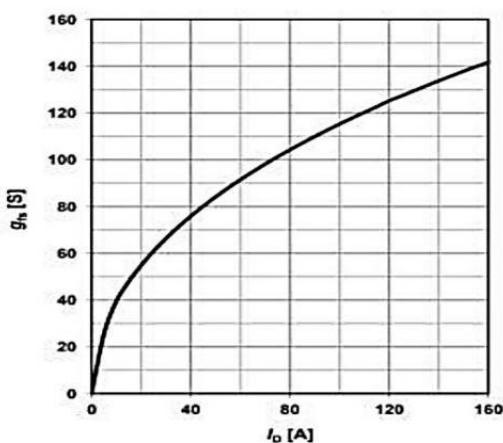


Figure4: forward transconductance

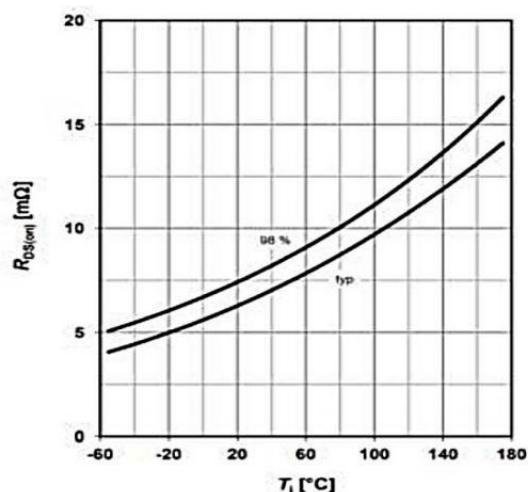


Figure5: Drain-source on-state resistance

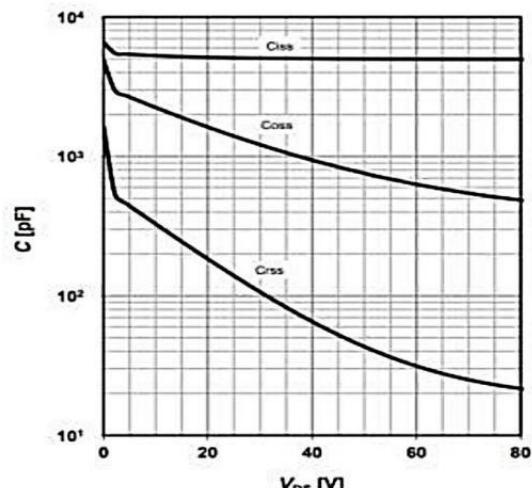


Figure6: Typ. capacitances

Typical Characteristics

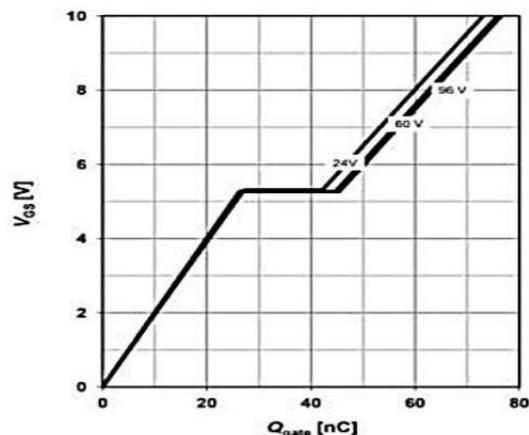


Figure7: Typ. gate charge

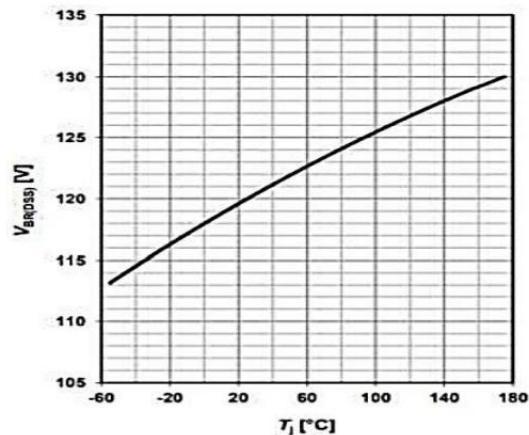


Figure8: Drain-source breakdown voltage

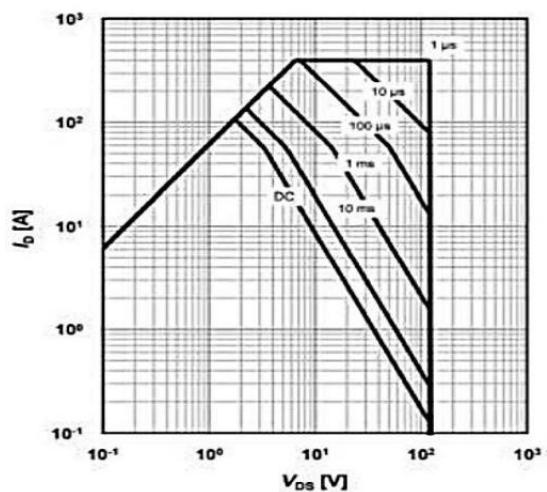


Figure9: Safe operating area

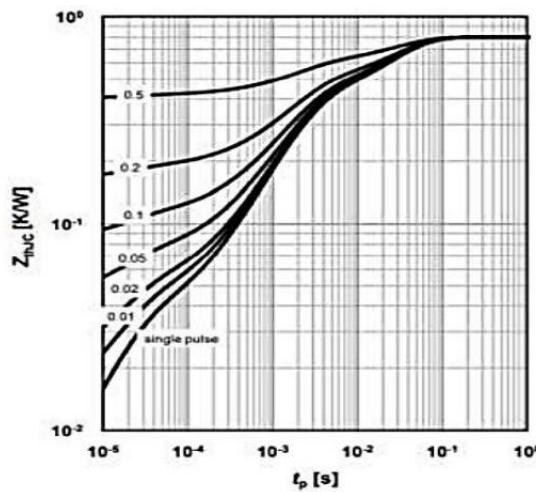
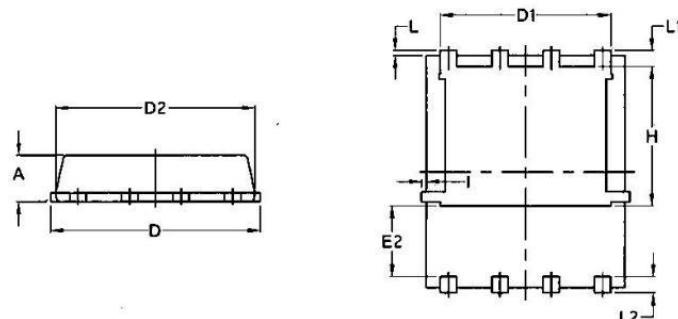
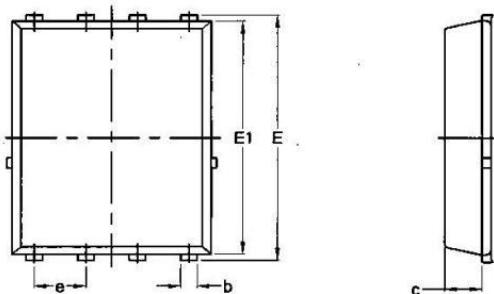


Figure10: Max. transient thermal impedance

Package Mechanical Data- PDFN5*6-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN5*6-8L		5000